

20 V, 4 A P-channel Trench MOSFET Rev. 1 — 11 March 2011

Product data sheet

Product profile 1.

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 1.8 V drain-source on-state resistance rated
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	<u>[1]</u>	-	-	-4	А
Static char	acteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = -4.5 V; I _D = -2.4 A; T _j = 25 °C		-	32	36	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source		
3	D	drain	1 ☐ ☐ 2 SOT23 (TO-236AB)	G G
				017aaa094

3. Ordering information

Table 3.	Ordering in	formation		
Type number Package		Package		
		Name	Description	Version
PMV32UP		TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
PMV32UP	NF%

[1] % = placeholder for manufacturing site code

5. Limiting values

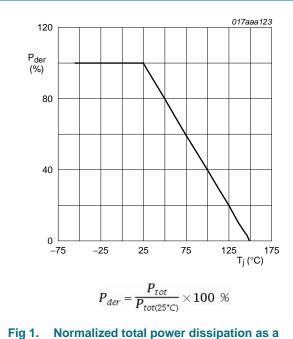
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

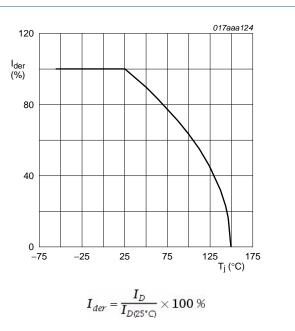
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	$T_j = 25 \ ^{\circ}C$		-	-20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	<u>[1]</u>	-	-4	А
		V_{GS} = -4.5 V; T_{amb} = 100 °C	<u>[1]</u>	-	-2.5	А
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$		-	-16	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW
			[1]	-	930	mW
		T _{sp} = 25 °C		-	4150	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
ls	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-1	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



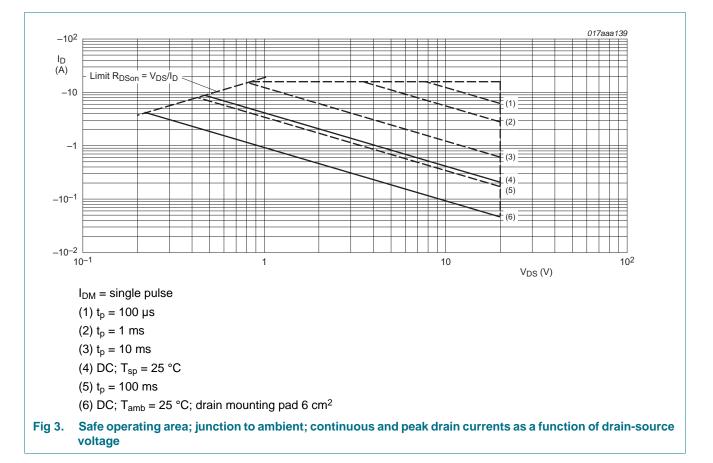
function of junction temperature





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6. Thermal characteristics

Table 6. Thermal characteristics

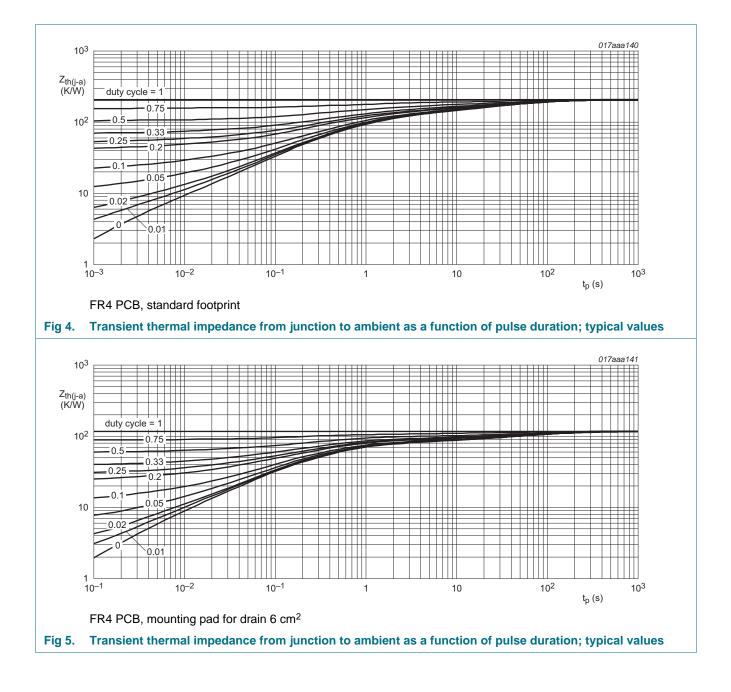
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	<u>[1]</u>	-	207	245	K/W
	from junction to ambient		[2]	-	117	135	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	30	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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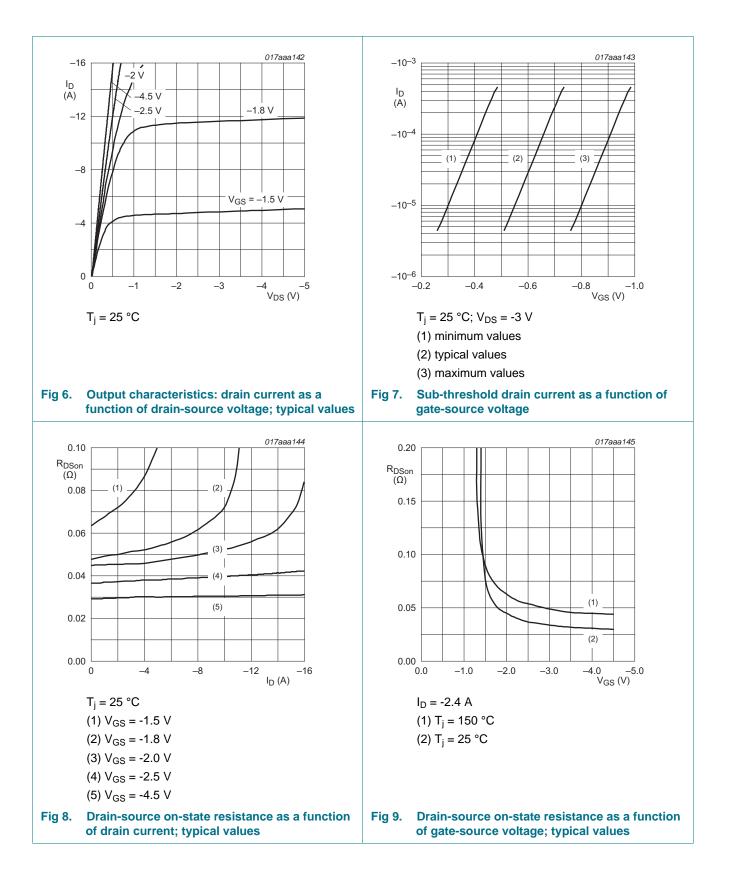
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7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$	-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μA
I _{GSS}	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; \text{T}_{j} = 25 ^{\circ}\text{C}$	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I _D = -2.4 A; T _j = 25 °C	-	32	36	mΩ
	resistance	V_{GS} = -4.5 V; I _D = -2.4 A; T _j = 150 °C	-	46	53	mΩ
		V_{GS} = -2.5 V; I _D = -2.0 A; T _j = 25 °C	-	40	46	mΩ
		V_{GS} = -1.8 V; I _D = -1.8 A; T _j = 25 °C	-	55	73	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -5 \text{ V}; \text{ I}_{D} = -2.4 \text{ A}; \text{ T}_{j} = 25 \text{ °C}$	-	13	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	I_D = -1 A; V_{DS} = -10 V; V_{GS} = -4.5 V;	-	15.5	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.7	-	nC
Q _{GD}	gate-drain charge		-	2.2	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = -10 V; f = 1 MHz;$	-	1890	-	pF
C _{oss}	output capacitance	$T_j = 25 \ ^{\circ}C$	-	175	-	pF
C _{rss}	reverse transfer capacitance		-	112	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; V_{GS} = -5 V; $R_{G(ext)}$ = 6 Ω ;	-	13	-	ns
t _r	rise time	T _j = 25 °C; I _D = -1 A	-	21	-	ns
t _{d(off)}	turn-off delay time		-	95	-	ns
t _f	fall time		-	33	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = -2.4 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.75	-1	V

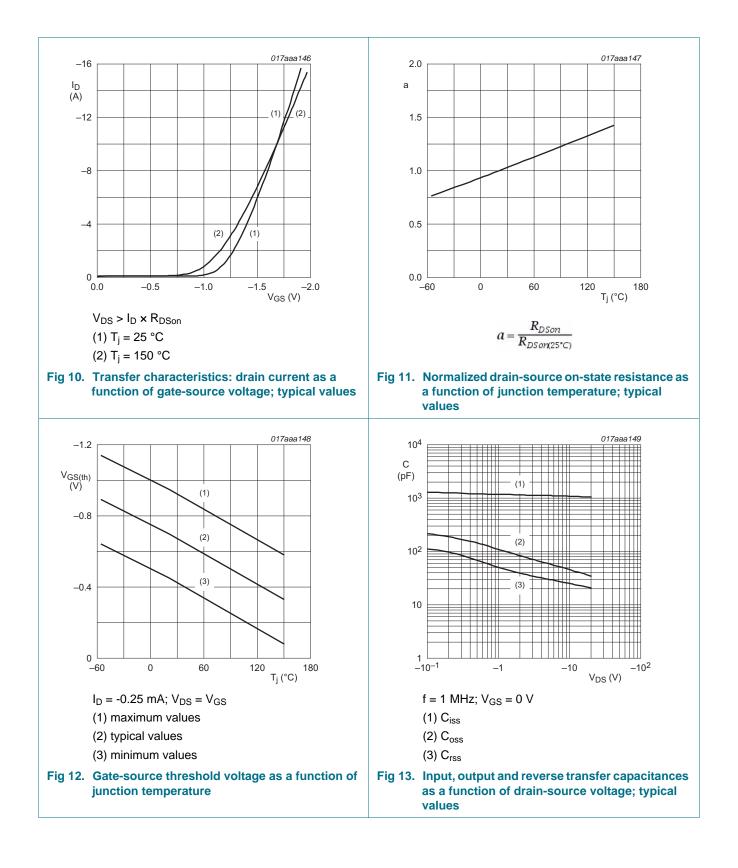
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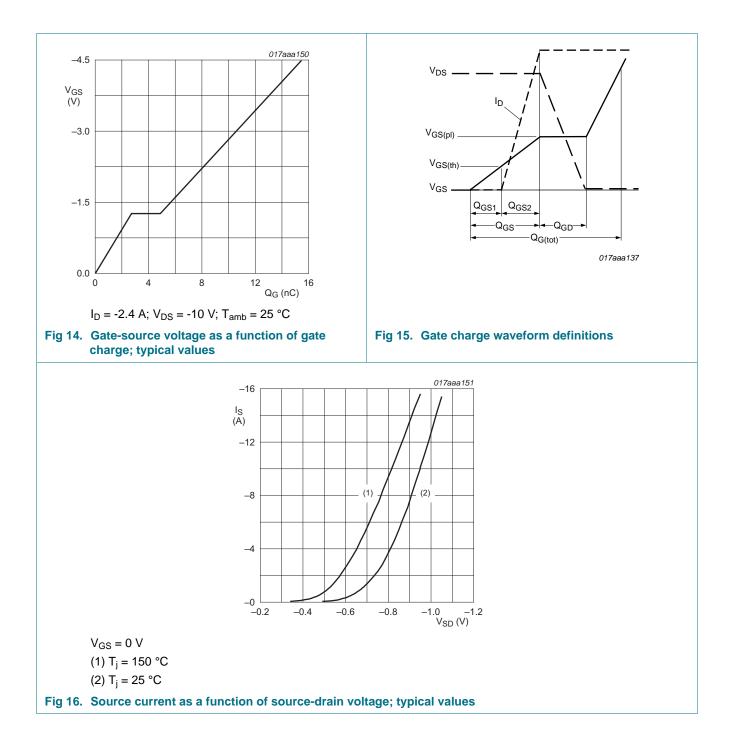
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8. Package outline

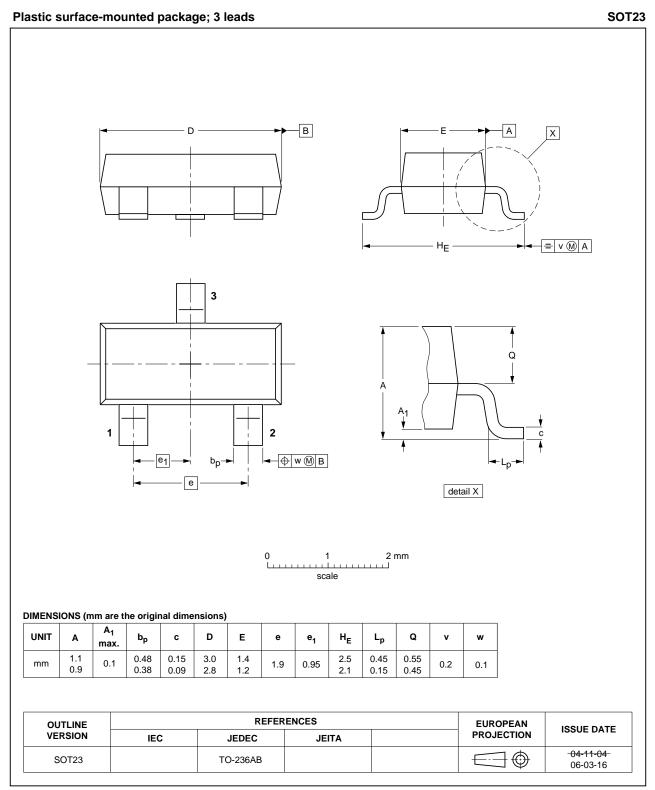
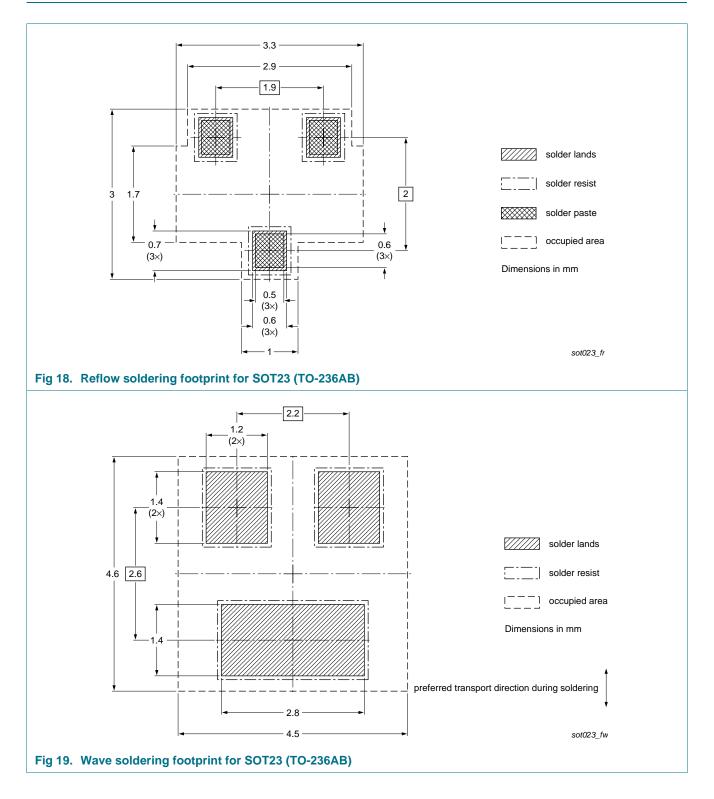


Fig 17. Package outline SOT23 (TO-236AB)

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9. Soldering



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10. Revision history

Table 8.	Revision history					
Document	ID	Release date	Data sheet status	Change notice	Supersedes	
PMV32UP	v.1	20110311	Product data sheet	-	-	

11. Legal information

11.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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